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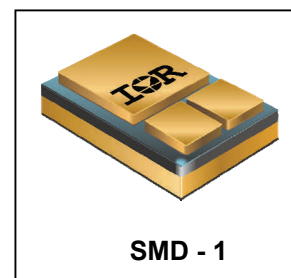
IRFN140
JANTX2N7218U
JANTXV2N7218U

POWER MOSFET
SURFACE MOUNT (SMD-1)

100V, N-CHANNEL
REF: MIL-PRF-19500/596

HEXFET® MOSFET TECHNOLOGY**Product Summary**

Part Number	RDS(on)	I _D
IRFN140	0.077Ω	28A

**Description**

HEXFET® MOSFET technology is the key to IR HiRel advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high trans conductance. HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and virtually any application where high reliability is required. The HEXFET transistor's totally isolated package eliminates the need for additional isolating material between the device and the heatsink. This improves thermal efficiency and reduces drain capacitance.

Features

- Simple Drive Requirements
- Hermetically Sealed
- Surface Mount
- Dynamic dv/dt Rating
- Light Weight
- ESD Rating: Class 2 per MIL-STD-750, Method 1020

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I _{D1} @ V _{GS} = 10V, T _C = 25°C	Continuous Drain Current	28	A
I _{D2} @ V _{GS} = 10V, T _C = 100°C	Continuous Drain Current	20	
I _{DM} @ T _C = 25°C	Pulsed Drain Current ①	112	
P _D @ T _C = 25°C	Maximum Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy ②	250	mJ
I _{AR}	Avalanche Current ①	28	A
E _{AR}	Repetitive Avalanche Energy ①	12.5	mJ
dv/dt	Peak Diode Recovery ③	5.5	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (for 5seconds)	
	Weight	2.6 (Typical)	

For footnotes refer to the page 2.

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.13	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.077	Ω	V _{GS} = 10V, I _{D2} = 20A ④
		—	—	0.125		V _{GS} = 10V, I _{D1} = 28A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
G _{fs}	Forward Transconductance	9.1	—	—	S	V _{DS} = 15V, I _{D2} = 20A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V _{DS} = 80V, V _{GS} = 0V
		—	—	250		V _{DS} = 80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _G	Total Gate Charge	—	—	59	nC	I _{D1} = 28A
Q _{GS}	Gate-to-Source Charge	—	—	16		V _{DS} = 50V
Q _{GD}	Gate-to-Drain ('Miller') Charge	—	—	30.7		V _{GS} = 10V
t _{d(on)}	Turn-On Delay Time	—	—	21	ns	V _{DD} = 50V
t _r	Rise Time	—	—	105		I _{D1} = 20A
t _{d(off)}	Turn-Off Delay Time	—	—	64		R _G = 9.1Ω
t _f	Fall Time	—	—	65		V _{GS} = 10V
L _S + L _D	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	1600	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	550	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	120	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	28	A	
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	112		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _J = 25°C, I _S = 28A, V _{GS} = 0V④
t _{rr}	Reverse Recovery Time	—	—	400	ns	T _J = 25°C ,I _F = 28A,V _{DD} ≤ 30V di/dt = 100A/μs ④
Q _{rr}	Reverse Recovery Charge	—	—	2.9	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	—	1.0	°C/W
R _{θJ-PCB}	Junction-to-PC board	—	4.0	—	

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V_{DD} = 25V, starting T_J = 25°C, L = 0.64mH, Peak I_L = 28A, V_{GS} = 10V.
- ③ I_{SD} ≤ 28A, di/dt ≤ 170A/μs, V_{DD} ≤ 100V, T_J ≤ 150°C.
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%

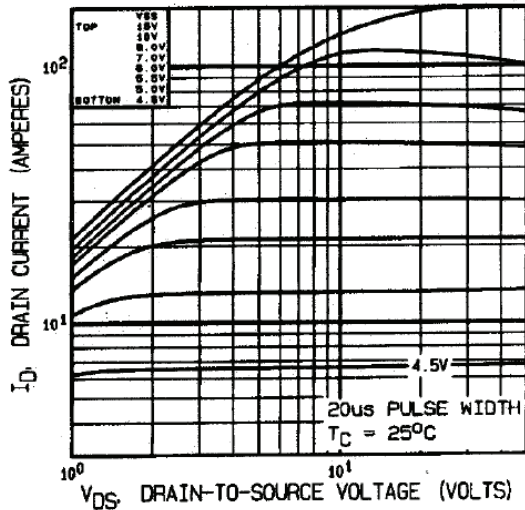


Fig 1. Typical Output Characteristics

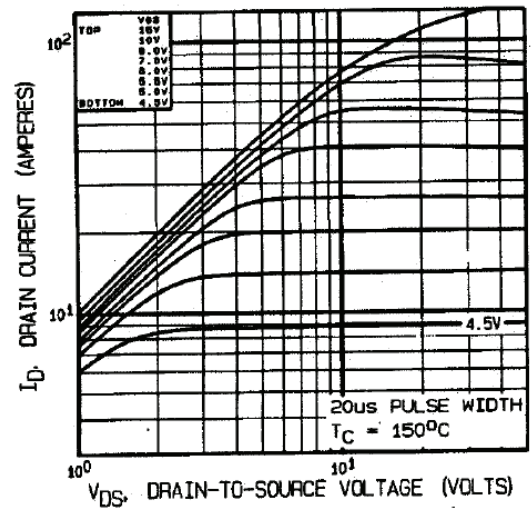


Fig 2. Typical Output Characteristics

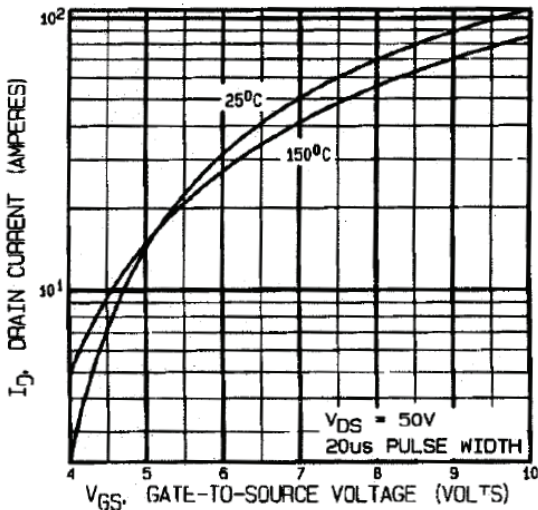


Fig 3. Typical Transfer Characteristics

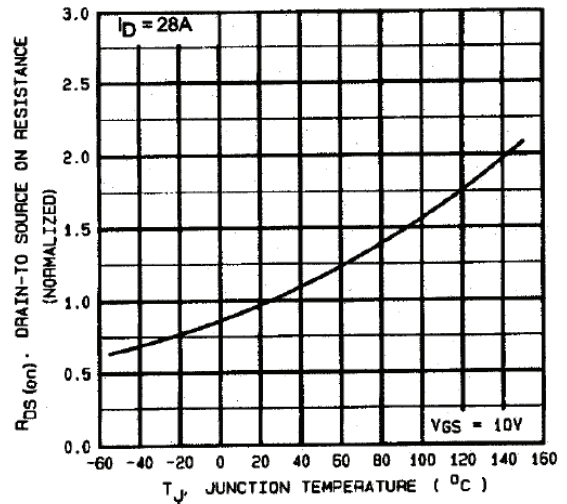


Fig 4. Normalized On-Resistance Vs. Temperature

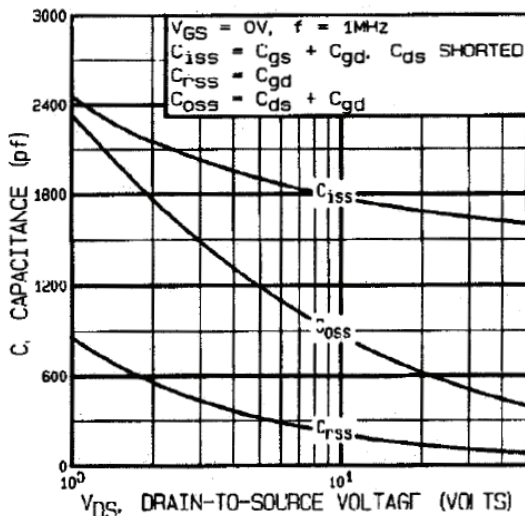


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

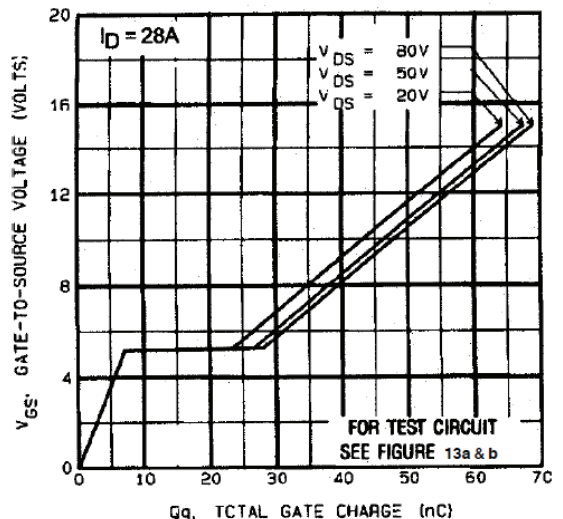


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

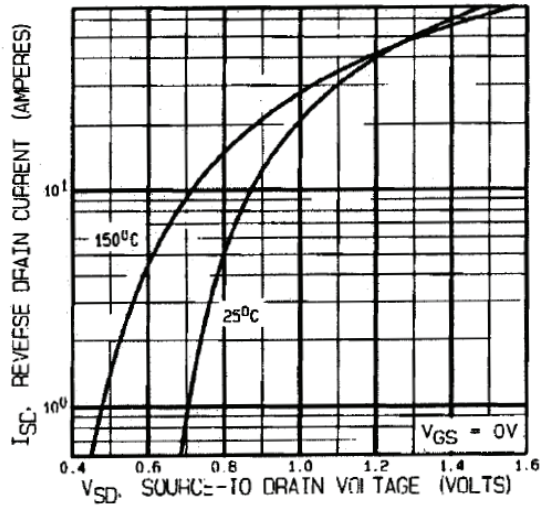


Fig 7. Typical Source-Drain Diode Forward Voltage

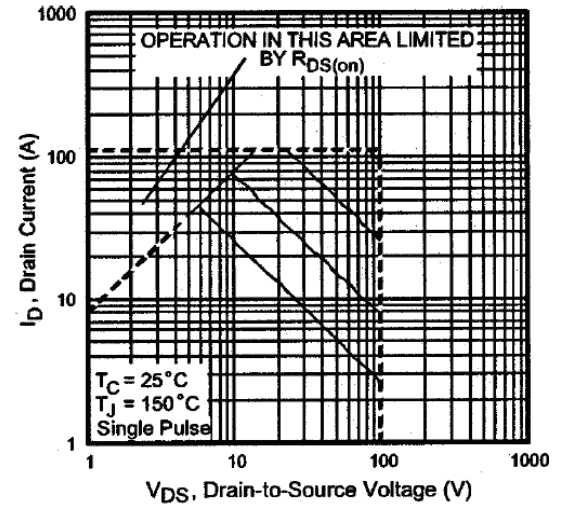


Fig 8. Maximum Safe Operating Area

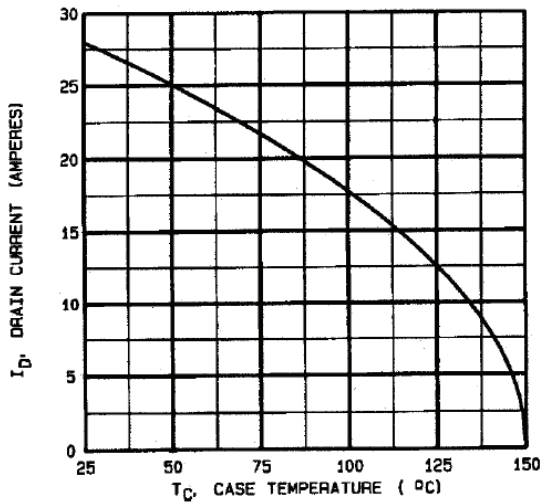


Fig 9. Maximum Drain Current Vs. Case Temperature

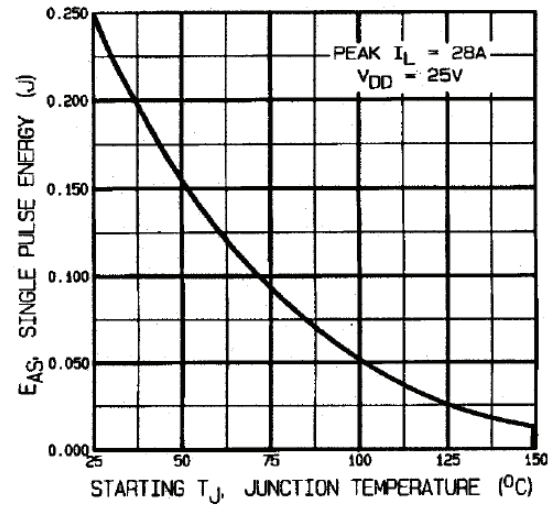


Fig 10. Maximum Avalanche Energy Vs. Drain Current

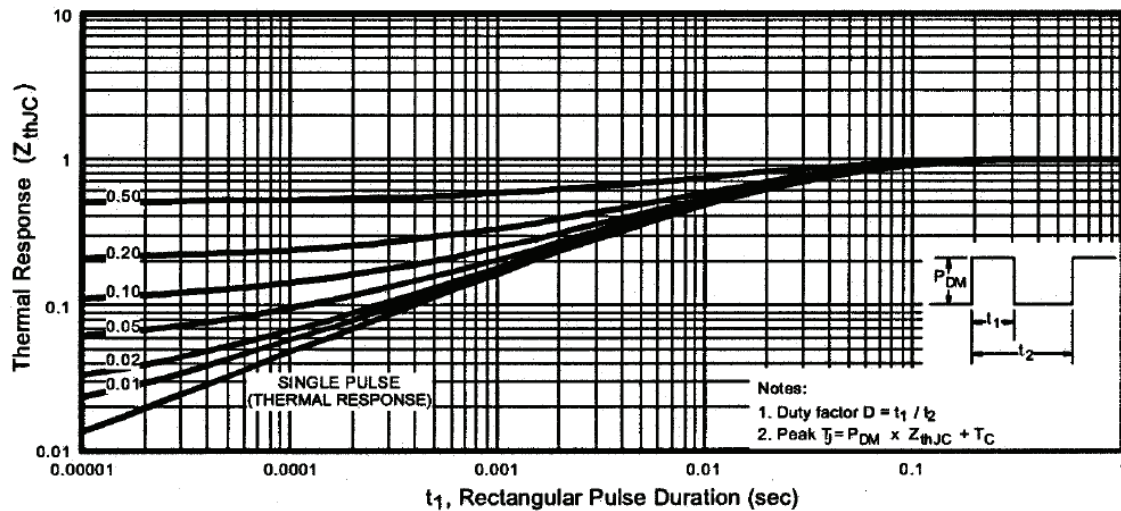


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

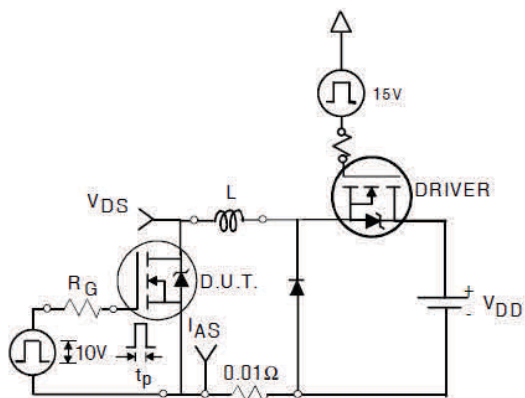


Fig 12a. Unclamped Inductive Test Circuit

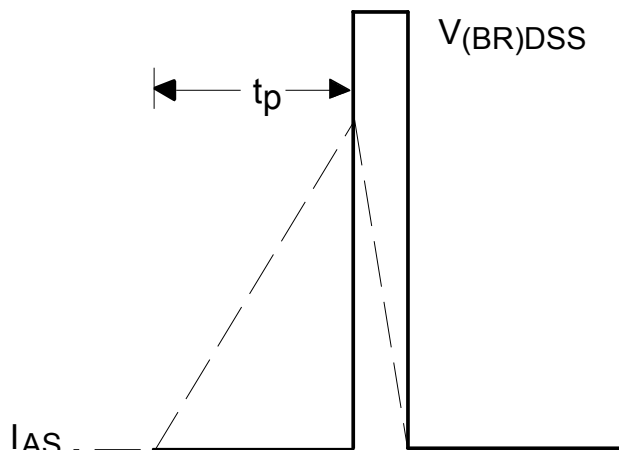


Fig 12b. Unclamped Inductive Waveforms

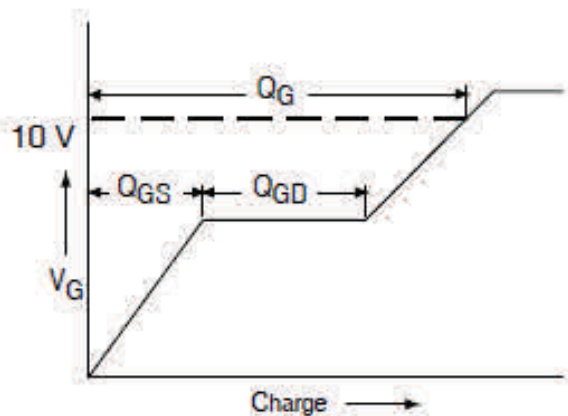


Fig 13a. Gate Charge Waveform

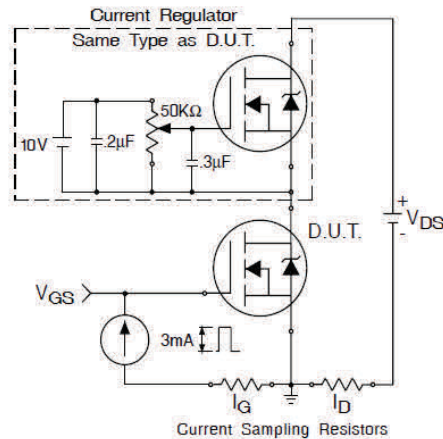


Fig 13b. Gate Charge Test Circuit

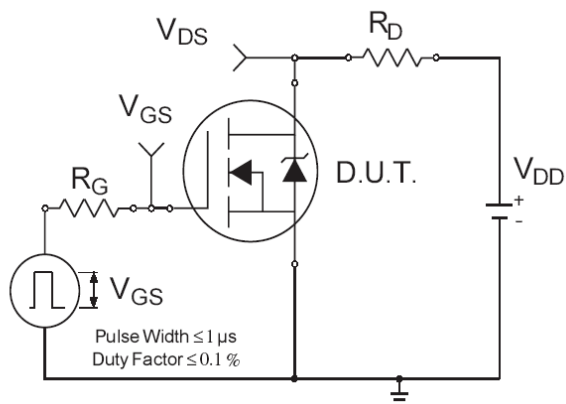


Fig 14a. Switching Time Test Circuit

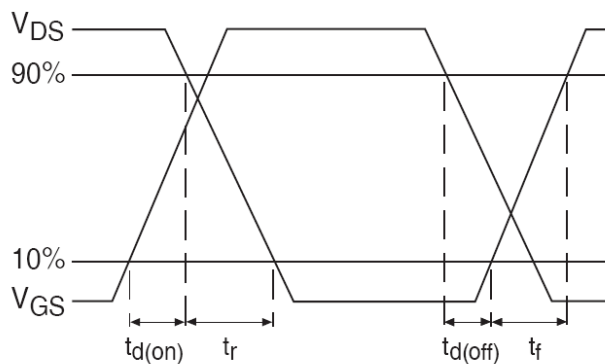
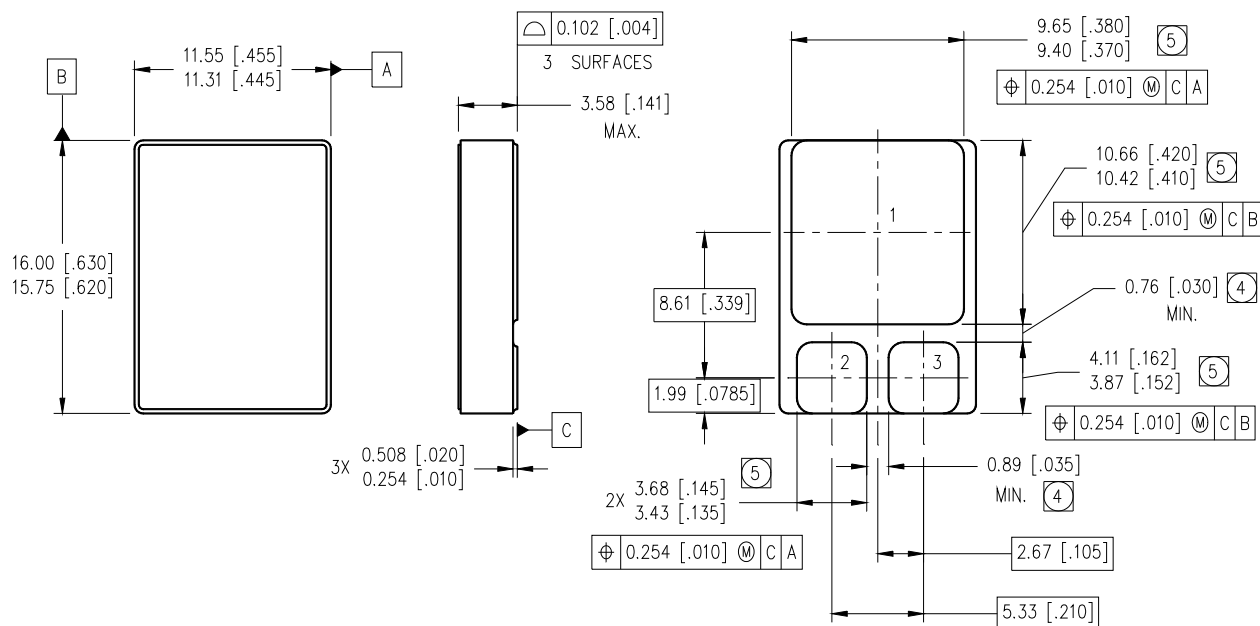


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions - SMD-1



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. DIMENSION INCLUDES METALLIZATION FLASH.
5. DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

MOSFET	SCHOTTKY SINGLE DIE	SCHOTTKY DUAL DIE
1 = DRAIN	1 = CATHODE	1 = CATHODE
2 = GATE	2 = COMMON ANODE	2 = ANODE 1
3 = SOURCE	3 = COMMON ANODE	3 = ANODE 2

IMPORTANT NOTICE

The information given in this document shall be in no event regarded as guarantee of conditions or characteristic. The data contained herein is a characterization of the component based on internal standards and is intended to demonstrate and provide guidance for typical part performance. It will require further evaluation, qualification and analysis to determine suitability in the application environment to confirm compliance to your system requirements.

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